

IN THE SPECIFICATION:

(Page 1, lines 16-22): A ferroelectric random access memory (FeRAM or FRAM) is a memory, which uses a ferroelectric capacitor that has a capacitor dielectric layer formed from a ferroelectric, is made non-volatile by the retention of polarization, and is made rewritable by the inversion of polarization.

Examples of the ferroelectric used include $\text{Pb}(\text{Zr}, \text{Ti})\text{O}_3$ (PZT), $(\text{Ba}, \text{Sr})\text{TiO}_3$ (BST), $\text{Bi}_{4-x}\text{La}_x\text{Ti}_3\text{O}_{12}$ (BLT), $[[\text{SrBi}_2\text{Ta}_2\text{O}_9]]$ $\text{SrBi}_2\text{Ta}_2\text{O}_9$ (SBT), etc. Here, the expression (A, B) indicates A_xB_{1-x} .

(Page 13, line 24 to page 14, line 3): Though this invention has been described above by way of embodiments, this invention is not limited thereto. Though the case where an SRO layer is used as one of the laminated upper electrodes was described, CaRuO_3 and LaRuO_3 are Ru oxides with the same perovskite crystal structure as SrRuO_3 , and thus the same effects as an SrRuO_x layer can be anticipated by use of a CaRuO_x layer or an LaRuO_x layer. LaNiO_3 and (La, Sr) CoO_3 $[[\text{CO}_3]]$ are also oxides with perovskite crystal structures and the same effects can be anticipated with these oxides as well.